

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY							
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^a	Q _g (Typ.)				
- 30	0.049 at V _{GS} = - 10 V	- 4.8	5.1 nC				
	0.054 at $V_{GS} = -4.5 \text{ V}$	- 4.1	5.1110				

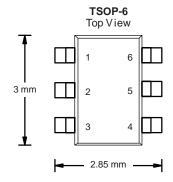
FEATURES

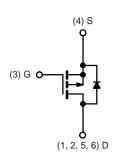
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET

COMPLIANT HALOGEN FREE

APPLICATIONS

· Load Switch





P-Channel MOSFET

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	- 30	V	
Gate-Source Voltage		V_{GS}	± 20	v
	T _C = 25 °C		- 4.8	
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C		- 4.1	
Continuous Diam Current (1) = 130 °C)	T _A = 25 °C	I _D	- 4.0 ^{b, c}	
	T _A = 70 °C		- 3.5 ^{b, c}	A
Pulsed Drain Current		I _{DM} - 20		
	T _C = 25 °C	_	- 2.5	
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	- 1.67 ^{b, c}	
	T _C = 25 °C		3.0	
Maximum Dawar Dissination	T _C = 70 °C	D.	2.0	w
Maximum Power Dissipation	T _A = 25 °C	- P _D	2.0 ^{b, c}	VV
	T _A = 70 °C		1.3 ^{b, c}	
Operating Junction and Storage Temperature	T _J , T _{stq}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Typical	Maximum	Unit			
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R_{thJA}	55	62.5	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	34	41	C/ V V		

Notes:

- a. Based on T_C = 25 °C.
 b. Surface Mounted on 1" x 1" FR4 board.
- d. Maximum under Steady State conditions is 110 °C/W.

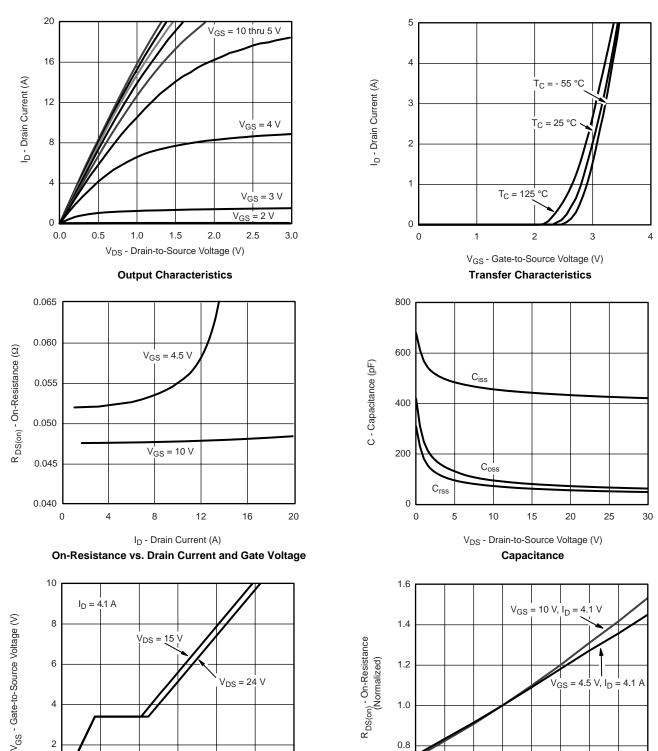


Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static					I.	•
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 30			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 31		mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μA		4.5		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.5		- 2.0	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zana Oata Valtana Busis Osumast		$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			- 10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 20			Α
	<u> </u>	V _{GS} = - 10 V, I _D = - 4.1 A		0.049		Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 1.0 A		0.054		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 4.1 A		8		S
Dynamic ^b						<u> </u>
Input Capacitance	C _{iss}			450		pF
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		80		
Reverse Transfer Capacitance	C _{rss}			63		
Total Gate Charge	Qg	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 4.1 A		10	15	nC
				5.1	8	
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.1 \text{ A}$		1.8		
Gate-Drain Charge	Q_{gd}			2.5		
Gate Resistance	R _g	f = 1 MHz		7		Ω
Turn-On Delay Time	t _{d(on)}			40	60	ns
Rise Time	t _r	V_{DD} = - 15 V, R_L = 4.6 Ω		80	120	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -3.3 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		20	30	
Fall Time	t _f			12	20	
Turn-On Delay Time	t _{d(on)}			5	10	
Rise Time	t _r	V_{DD} = - 15 V, R_L = 4.6 Ω		13	20	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 3.3 A, V_{GEN} = - 10 V, R_g = 1 Ω		20	30	
Fall Time	t _f			10	15	
Drain-Source Body Diode Characteristi	cs			•		
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 2.5	_
Pulse Diode Forward Current ^a	I _{SM}				- 20	A
Body Diode Voltage	V _{SD}	I _S = - 3.3 A		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}			20	30	ns
Body Diode Reverse Recovery Charge	Q _{rr}	1 22 A di/dt 100 A/v.c T 25 °C		20	30	nC
Reverse Recovery Fall Time	t _a	$I_F = -3.3 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$		14		
Reverse Recovery Rise Time	t _b			6		ns

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 % b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





0.8

0.6

- 50

- 25

0

25

50

T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature

75

100

125 150

服务热线:400-655-8788

2

0

0

2

6

Q_q - Total Gate Charge (nC)

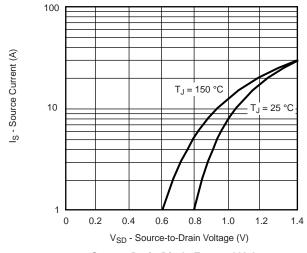
Gate Charge

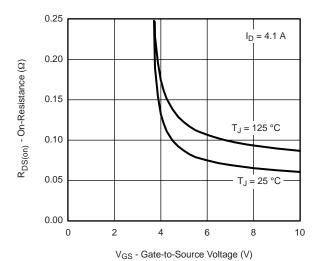
8

10

12

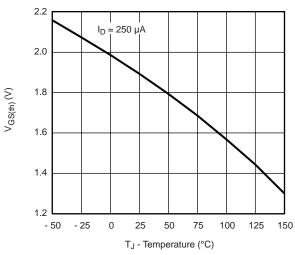


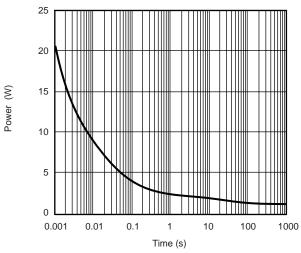




Source-Drain Diode Forward Voltage

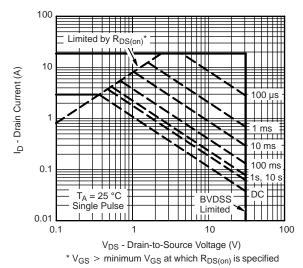






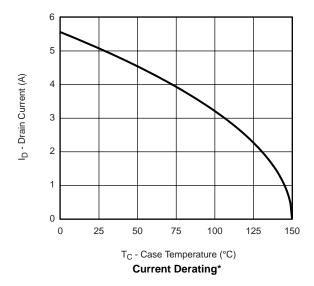
Threshold Voltage

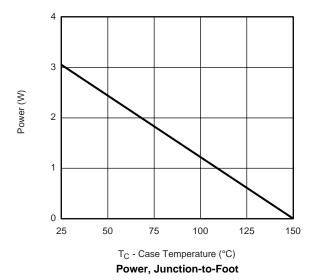
Single Pulse Power



Safe Operating Area

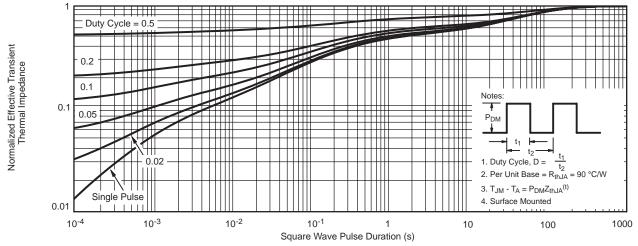




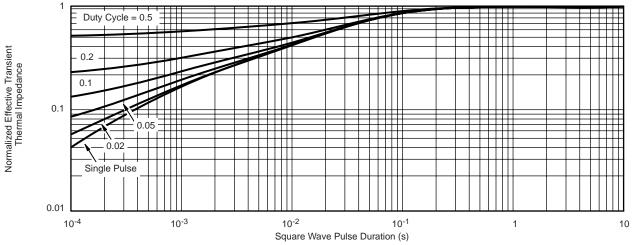


^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient

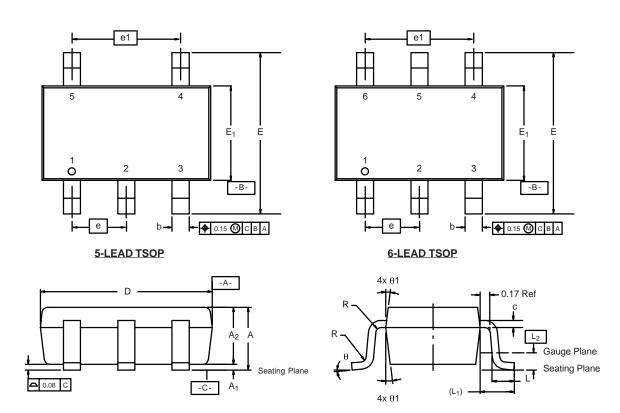


Normalized Thermal Transient Impedance, Junction-to-Foot



TSOP: 5/6-LEAD

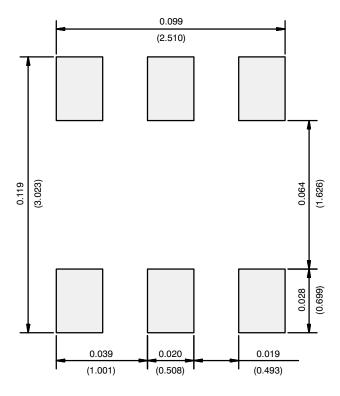
JEDEC Part Number: MO-193C



	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
E	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	1	0.020	
L ₁	0.60 Ref			0.024 Ref			
L ₂	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	1	-	
θ	0°	4°	8°	0°	4°	8°	
θ_1	7° Nom			7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							



RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads Dimensions in Inches/(mm)



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